GDDR5 SGRAM

EDW4032BABG – 8 Meg x 32 I/O x 16 banks, 16 Meg x 16 I/O x 16 banks

Features

- $V_{DD} = V_{DDQ} = 1.6V/1.55V/1.5V \pm 3\%$ and $1.35V \pm 3\%$
- Data rate: 6.0 Gb/s, 7.0 Gb/s, 8.0 Gb/s
- 16 internal banks
- Four bank groups for $^tCCDL = 3$ ^tCK
- $8n$-bit prefetch architecture: 256-bit per array read or write access for x32; 128-bit for x16
- Burst length (BL): 8 only
- Programmable CAS latency: 7–25
- Programmable WRITE latency: 4–7
- Programmable CRC READ latency: 2–3
- Programmable CRC WRITE latency: 8–14
- Programmable EDC hold pattern for CDR
- Precharge: Auto option for each burst access
- Auto refresh and self refresh modes
- Refresh cycles: 16,384 cycles/32ms
- Interface: Pseudo open drain (POD-15) compatible outputs: 40Ω pull-down, 60Ω pull-up
- On-die termination (ODT): 60Ω or 120Ω (NOM)
- ODT and output driver strength auto calibration with external resistor ZQ pin: 120Ω
- Programmable termination and driver strength offsets
- Selectable external or internal V_{REF} for data inputs; programmable offsets for internal V_{REF}
- Separate external V_{REF} for address/command inputs
- $T_C = 0°C$ to $+95°C$
- x32/x16 mode configuration set at power-up with EDC pin
- Single-ended interface for data, address, and command
- Quarter data rate differential clock inputs CK_t, CK_c for address and commands
- Two half data rate differential clock inputs, WCK_t and WCK_c, each associated with two data bytes (DQ, DBI_n, EDC)
- DDR data (WCK) and addressing (CK)
- SDR command (CK)
- Write data mask function via address bus (single/ double byte mask)
- Data bus inversion (DBI) and address bus inversion (ABI)
- Input/output PLL on/off mode
- Duty cycle corrector (DCC) for data clock (WCK)
- Digital RAS lockout

- Address training: Address input monitoring via DQ pins
- WCK2CK clock training: Phase information via EDC pins
- Data read and write training via read FIFO (FIFO depth = 6)
- Read FIFO pattern preloaded by LDFF command
- Direct write data load to read FIFO by WRTR command
- Consecutive read of read FIFO by RDTR command
- Read/write data transmission integrity secured by cyclic redundancy check (CRC-8)
- Read/write EDC on/off mode
- Low power modes
- RDQS mode on EDC pin
- On-die temperature sensor with readout
- Automatic temperature sensor controlled self refresh rate
- Vendor ID, FIFO depth and density info fields for identification
- Mirror function with MF pin
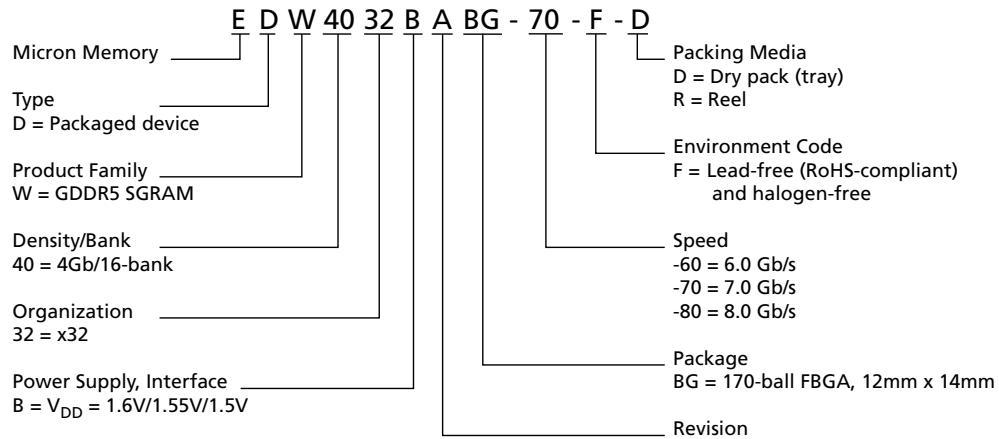- Boundary scan function with SEN pin

Options[1]   Marking

- Organization
  - Density   40
  - 128 Meg x 32 (words x bits)   32
- FBGA package
  - 170-ball (12mm x 14mm)   BG
- Package environment code
  - Lead- and halogen-free   -F
    (RoHS-compliant)
- Package media
  - Dry pack (tray)   -D
  - Reel   -R
- Timing – maximum data rate
  - 6.0 Gb/s, 5.0 Gb/s   -60
  - 7.0 Gb/s, 6.0 Gb/s   -70
  - 8.0 Gb/s, 6.0 Gb/s   -80
- Operating temperature
  - Commercial ($0°C \leq T_C \leq +95°C$)   None
- Revision   A

Note: 1.   Not all options listed can be combined to define an offered product. Use the part catalog search on http://www.micron.com for available offerings.

Figure 1: Part Numbering

E D W 40 32 B A BG - 70 - F - D

Micron Memory

Type
D = Packaged device

Product Family
W = GDDR5 SGRAM

Density/Bank
40 = 4Gb/16-bank

Organization
32 = x32

Power Supply, Interface
B = V_{DD} = 1.6V/1.55V/1.5V

Packing Media
D = Dry pack (tray)
R = Reel

Environment Code
F = Lead-free (RoHS-compliant)
and halogen-free

Speed
-60 = 6.0 Gb/s
-70 = 7.0 Gb/s
-80 = 8.0 Gb/s

Package
BG = 170-ball FBGA, 12mm x 14mm

Revision

Note: 1. This Micron GDDR5 SGRAM is available in different speed bins. The operating range and AC timings of a faster speed bin are a superset of all slower speed bins. Therefore it is safe to use a faster bin device as a drop-in replacement of a slower bin device when operated within the supply voltage and frequency range of the slower bin device.

FBGA Part Marking Decoder

Due to space limitations, FBGA-packaged components have an abbreviated part marking that is different from the part number. For a quick conversion of an FBGA code, see the FBGA Part Marking Decoder on Micron's web site: http://www.micron.com.

Ball Assignments and Descriptions

Figure 2: 170-Ball FBGA – MF = 0 (Top View)

	1	2	3	4	5	6	7	8	9	10	11	12	13	14
A	V_{SSQ}	DQ1	V_{SSQ}	DQ0	NC					V_{REFD}	DQ8	V_{SSQ}	DQ9	V_{SSQ}
B	V_{DDQ}	DQ3	V_{DDQ}	DQ2	V_{SS}					V_{SS}	DQ10	V_{DDQ}	DQ11	V_{DDQ}
C	V_{SSQ}	EDC0	V_{SSQ}	V_{SSQ}	V_{DD}					V_{DD}	V_{SSQ}	V_{SSQ}	EDC1	V_{SSQ}
D	V_{DDQ}	DBI0_n	V_{DDQ}	WCK01_t	WCK01_c					V_{SS}	V_{DD}	V_{DDQ}	DBI1_n	V_{DDQ}
E	V_{SSQ}	DQ5	V_{SSQ}	DQ4	V_{DDQ}					V_{DDQ}	DQ12	V_{SSQ}	DQ13	V_{SSQ}
F	V_{DDQ}	DQ7	V_{DDQ}	DQ6	V_{SSQ}					V_{SSQ}	DQ14	V_{DDQ}	DQ15	V_{DDQ}
G	V_{DD}	V_{DDQ}	RAS_n	V_{DD}	V_{SS}					V_{SS}	V_{DD}	CS_n	V_{DDQ}	V_{DD}
H	V_{SS}	V_{SSQ}	V_{DDQ}	A10, A0	A9, A1					BA3, A3	BA0, A2	V_{DDQ}	V_{SSQ}	V_{SS}
J	MF	RESET_n	CKE_n	ABI_n	A12, A13					SEN	CK_c	CK_t	ZQ	V_{REFC}
K	V_{SS}	V_{SSQ}	V_{DDQ}	A8, A7	A11, A6					BA1, A5	BA2, A4	V_{DDQ}	V_{SSQ}	V_{SS}
L	V_{DD}	V_{DDQ}	CAS_n	V_{DD}	V_{SS}					V_{SS}	V_{DD}	WE_n	V_{DDQ}	V_{DD}
M	V_{DDQ}	DQ31	V_{DDQ}	DQ30	V_{SSQ}					V_{SSQ}	DQ22	V_{DDQ}	DQ23	V_{DDQ}
N	V_{SSQ}	DQ29	V_{SSQ}	DQ28	V_{DDQ}					V_{DDQ}	DQ20	V_{SSQ}	DQ21	V_{SSQ}
P	V_{DDQ}	DBI3_n	V_{DDQ}	WCK23_t	WCK23_c					V_{SS}	V_{DD}	V_{DDQ}	DBI2_n	V_{DDQ}
R	V_{SSQ}	EDC3	V_{SSQ}	V_{SSQ}	V_{DD}					V_{DD}	V_{SSQ}	V_{SSQ}	EDC2	V_{SSQ}
T	V_{DDQ}	DQ27	V_{DDQ}	DQ26	V_{SS}					V_{SS}	DQ18	V_{DDQ}	DQ19	V_{DDQ}
U	V_{SSQ}	DQ25	V_{SSQ}	DQ24	NC					V_{REFD}	DQ16	V_{SSQ}	DQ17	V_{SSQ}

(Top view)

Data   Addresses   GDDR5   Supply   Ground

Note: 1. Balls shown with a heavy, solid outline are off in x16 mode.

Figure 3: 170-Ball FBGA – MF = 1 (Top View)

	1	2	3	4	5	6	7	8	9	10	11	12	13	14
A	V_{SSQ}	DQ25	V_{SSQ}	DQ24	NC					V_{REFD}	DQ16	V_{SSQ}	DQ17	V_{SSQ}
B	V_{DDQ}	DQ27	V_{DDQ}	DQ26	V_{SS}					V_{SS}	DQ18	V_{DDQ}	DQ19	V_{DDQ}
C	V_{SSQ}	EDC3	V_{SSQ}	V_{SSQ}	V_{DD}					V_{DD}	V_{SSQ}	V_{SSQ}	EDC2	V_{SSQ}
D	V_{DDQ}	DBI3_n	V_{DDQ}	WCK23_t	WCK23_c					V_{SS}	V_{DD}	V_{DDQ}	DBI2_n	V_{DDQ}
E	V_{SSQ}	DQ29	V_{SSQ}	DQ28	V_{DDQ}					V_{DDQ}	DQ20	V_{SSQ}	DQ21	V_{SSQ}
F	V_{DDQ}	DQ31	V_{DDQ}	DQ30	V_{SSQ}					V_{SSQ}	DQ22	V_{DDQ}	DQ23	V_{DDQ}
G	V_{DD}	V_{DDQ}	CAS_n	V_{DD}	V_{SS}					V_{SS}	V_{DD}	WE_n	V_{DDQ}	V_{DD}
H	V_{SS}	V_{SSQ}	V_{DDQ}	A8, A7	A11, A6					BA1, A5	BA2, A4	V_{DDQ}	V_{SSQ}	V_{SS}
J	MF	RESET_n	CKE_n	ABI_n	A12, A13					SEN	CK_c	CK_t	ZQ	V_{REFC}
K	V_{SS}	V_{SSQ}	V_{DDQ}	A10, A0	A9, A1					BA3, A3	BA0, A2	V_{DDQ}	V_{SSQ}	V_{SS}
L	V_{DD}	V_{DDQ}	RAS_n	V_{DD}	V_{SS}					V_{SS}	V_{DD}	CS_n	V_{DDQ}	V_{DD}
M	V_{DDQ}	DQ7	V_{DDQ}	DQ6	V_{SSQ}					V_{SSQ}	DQ14	V_{DDQ}	DQ15	V_{DDQ}
N	V_{SSQ}	DQ5	V_{SSQ}	DQ4	V_{DDQ}					V_{DDQ}	DQ12	V_{SSQ}	DQ13	V_{SSQ}
P	V_{DDQ}	DBI0_n	V_{DDQ}	WCK01_t	WCK01_c					V_{SS}	V_{DD}	V_{DDQ}	DBI1_n	V_{DDQ}
R	V_{SSQ}	EDC0	V_{SSQ}	V_{SSQ}	V_{DD}					V_{DD}	V_{SSQ}	V_{SSQ}	EDC1	V_{SSQ}
T	V_{DDQ}	DQ3	V_{DDQ}	DQ2	V_{SS}					V_{SS}	DQ10	V_{DDQ}	DQ11	V_{DDQ}
U	V_{SSQ}	DQ1	V_{SSQ}	DQ0	NC					V_{REFD}	DQ8	V_{SSQ}	DQ9	V_{SSQ}

(Top view)

Data	Addresses	GDDR5	Supply	Ground

Note: 1. Balls shown with a heavy, solid outline are off in x16 mode.

## Table 1: 170-Ball FBGA Ball Descriptions

Symbol	Type	Description
A[13:0]	Input	**Address inputs:** Provide the row address for ACTIVE commands. A[5:0] (A6) provide the column address and A8 defines the auto precharge bit for READ/WRITE commands, to select one location out of the memory array in the respective bank. A8 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A8 LOW, bank selected by BA[3:0]) or all banks (A8 HIGH). The address inputs also provide the op-code during a MODE REGISTER SET command and the data bits during LDFF commands. A[12:8] are sampled with the rising edge of CK_t and A[7:0], A13 are sampled with the rising edge of CK_c.
ABI_n	Input	**Address bus inversion:** Reduces the power requirements on address pins by limiting the number of address lines driving LOW to 5. ABI_n is enabled by the corresponding ABI mode register bit.
BA[3:0]	Input	**Bank address inputs:** Define the bank to which an ACTIVE, READ, WRITE, or PRECHARGE command is being applied. BA[3:0] define which mode register is loaded during the MODE REGISTER SET command. BA[3:0] are sampled with the rising edge of CK_t.
CK_t, CK_c	Input	**Clock:** CK_t and CK_c are differential clock inputs. Command inputs are latched on the rising edge of CK_t. Address inputs are latched on the rising edge of CK_t and the rising edge of CK_c. All latencies are referenced to CK_t. CK_t and CK_c are externally terminated.
WCK01_t, WCK01_c/ WCK23_t, WCK23_c	Input	**Data Clocks:** WCK_t and WCK_c are differential clocks used for write data capture and read data output. WCK01_t and WCK01_c are associated with DQ[15:0], DBI0_n, DBI1_n, EDC0, and EDC1. WCK23_t and WCK23_c are associated with DQ[31:16], DBI2_n, DBI3_n, EDC2, and EDC3. WCK clocks operate at nominally twice the CK clock frequency.
CKE_n	Input	**Clock enable:** CKE_n enables (registered LOW) and disables (registered HIGH) internal circuitry and clocks on the device. The specific circuitry that is enabled/disabled is dependent upon the device configuration and operating mode. Taking CKE_n HIGH provides PRECHARGE POWER-DOWN and SELF REFRESH operations (all banks idle), or active power-down (row active in any bank). CKE_n is synchronous for power-down entry and exit and for self refresh entry. CKE_n must be maintained LOW throughout read and write accesses. Input buffers (excluding CKE_n) are disabled during SELF REFRESH operation. The value of CKE_n latched at power-up with RESET_n going HIGH determines the termination value of the address and command inputs.
CS_n	Input	**Chip select:** CS_n enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS_n is registered HIGH, but internal command execution continues. CS_n is considered part of the command code.
MF	Input	**Mirror function:** V_{DDQ} CMOS input. Must be tied to V_{DDQ} or V_{SS}.
RAS_n, CAS_n, WE_n	Input	**Command inputs:** RAS_n, CAS_n, and WE_n (along with CS_n) define the command being entered.
RESET_n	Input	**Reset:** RESET_n is an active LOW CMOS input referenced to V_{SS}. A full chip reset may be performed at any time by pulling RESET_n LOW. With RESET_n LOW all ODTs are disabled.
SEN	Input	**Scan enable:** V_{DDQ} CMOS input. Must be tied to V_{SS} when not in use.

Table 1: 170-Ball FBGA Ball Descriptions (Continued)

Symbol	Type	Description
DQ[31:0]	I/O	**Data input/output:** Bidirectional 32-bit data bus.
DBI[3:0]_n	I/O	**Data bus inversion:** Reduces the DC power consumption and supply noise induced jitter on data pins. DBI0_n is associated with DQ[7:0], DBI1_n with DQ[15:8], DBI2_n with DQ[23:16], and DBI3_n with DQ[31:24].
EDC[3:0]	Output	**Error detection code:** The calculated CRC data is transmitted on these pins. In addition, these pins drive a hold pattern when idle and can be used as an RDQS function. EDC0 is associated with DQ[7:0], EDC1 with DQ[15:8], EDC2 with DQ[23:16], and EDC3 with DQ[31:24].
V_{DD}	Supply	**Power supply:** 1.6V/1.55V/1.5V ±3% and 1.35V ±3%.
V_{DDQ}	Supply	**DQ power supply:** 1.6V/1.55V/1.5V ±3% and 1.35V ±3%. Isolated on the device for improved noise immunity.
V_{REFC}	Supply	**Reference voltage for control and address:** V_{REFC} must be maintained at all times (including self refresh) for proper device operation.
V_{REFD}	Supply	**Reference voltage for data:** V_{REFD} must be maintained at all times (including self refresh) for proper device operation.
V_{SS}	Supply	Ground.
V_{SSQ}	Supply	**DQ ground:** Isolated on the device for improved noise immunity.
ZQ	Reference	**External reference ball for impedance calibration:** This ball is tied to an external 120Ω resistor (ZQ), which is tied to V_{SSQ}.
NC	–	**No connect:** These balls should be left unconnected (the ball has no connection to the device or to other balls).

Package Dimensions

Figure 4: 170-Ball FBGA (BG)
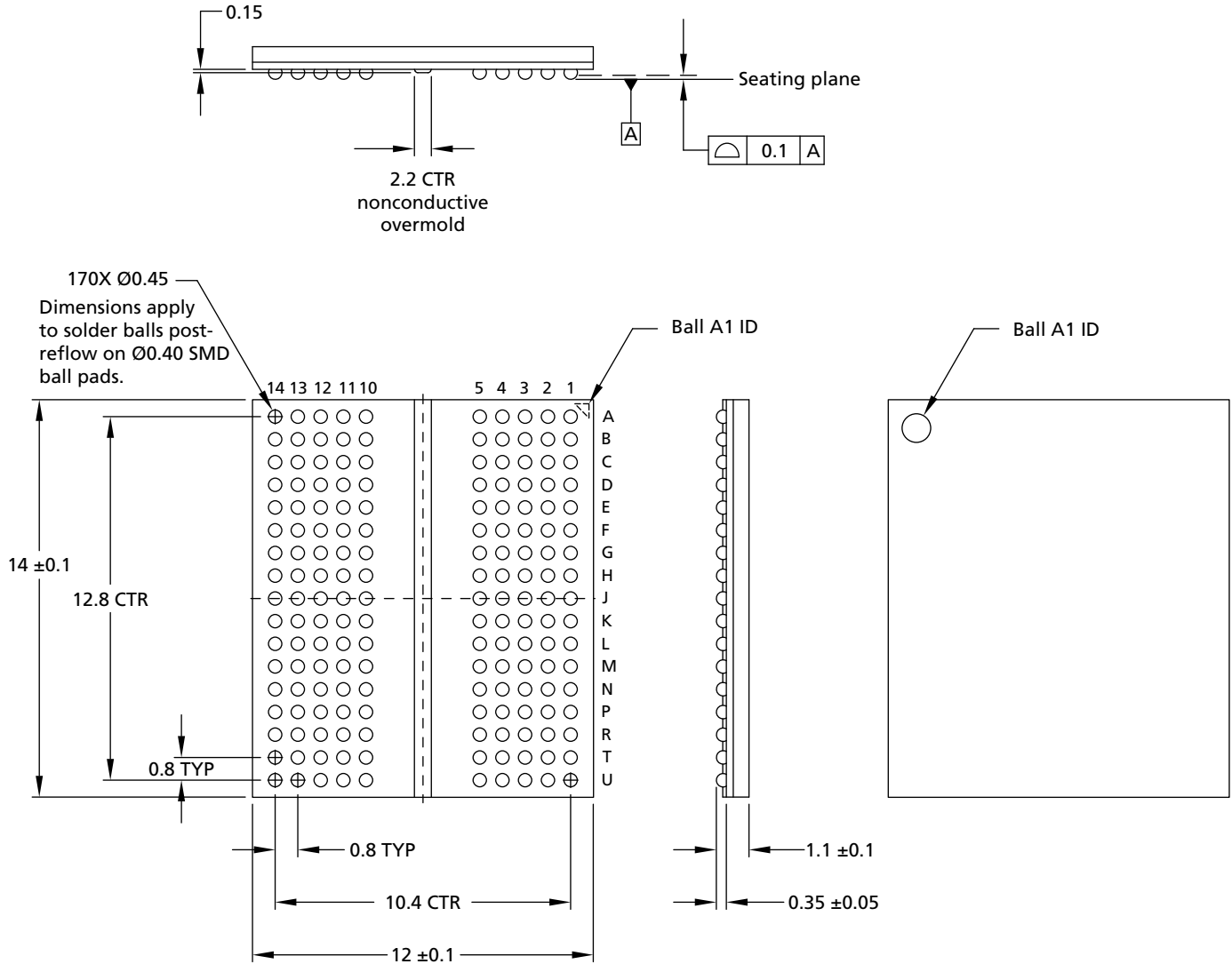
Notes: 1. All dimensions are in millimeters.
2. Solder ball material: SAC302 (96.8% Sn, 3% Ag, 0.2% Cu).

This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein.
Although considered final, these specifications are subject to change, as further product development and data characterization some-
times occur.